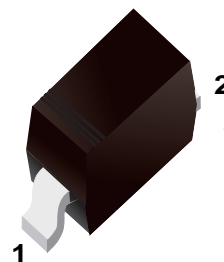


Schottky Diodes

■ Features

- Fast Switching Speed
- For General Purpose Switching Applications.
- High Conductance


■ Simplified outline(SOD-323)
■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Reverse Voltage	V_{RM}	10	V
Forward Current	I_F	3	A
Peak Forward Surge Current ($t \leq 10ms$)	I_{FM}	5	
Power Dissipation $T_S \leq 28^\circ C$	P_d	1350	mW
Thermal Resistance Junction to Point ¹	$R_{\theta JS}$	≤ 90	K/W
Junction Temperature	T_J	150	°C
Operating Temperature Range	T_{OP}	-55 to 85	
Storage Temperature range	T_{stg}	-55 to 150	

NOTES:

1.For calculation of R_{thJA} please refer to Application Note Thermal Resistance

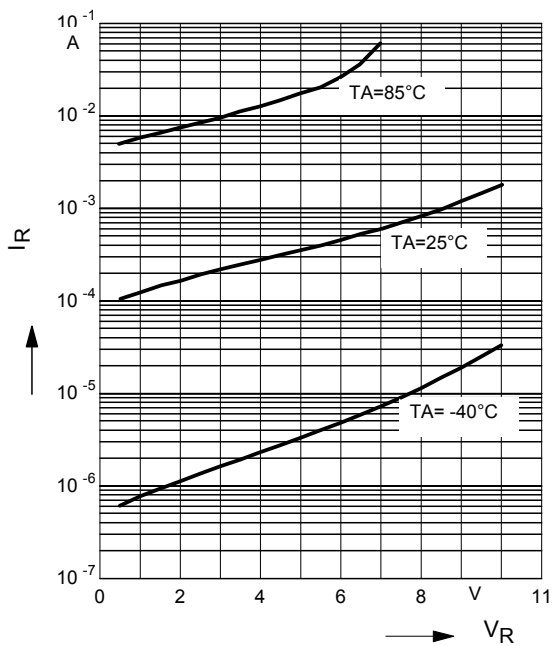
■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu A$	10			V
Forward voltage	V_F	$I_F = 10 mA$			0.15	
		$I_F = 100 mA$			0.23	
		$I_F = 1000 mA$			0.37	
Reverse voltage leakage current	I_R	$V_R = 5 V$			1	mA
		$V_R = 8 V$			2.6	
		$V_R = 5 V, T_A = 80^\circ C$		18		
Junction capacitance	C_j	$V_R = 5 V, f = 1 MHz$			35	pF

■ Typical Characteristics

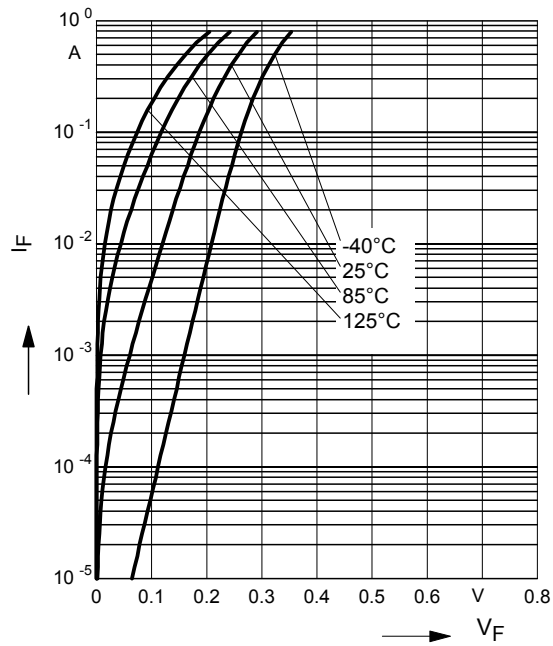
Reverse current $I_R = f(V_R)$

$T_A =$ Parameter



Forward current $I_F = f(V_F)$

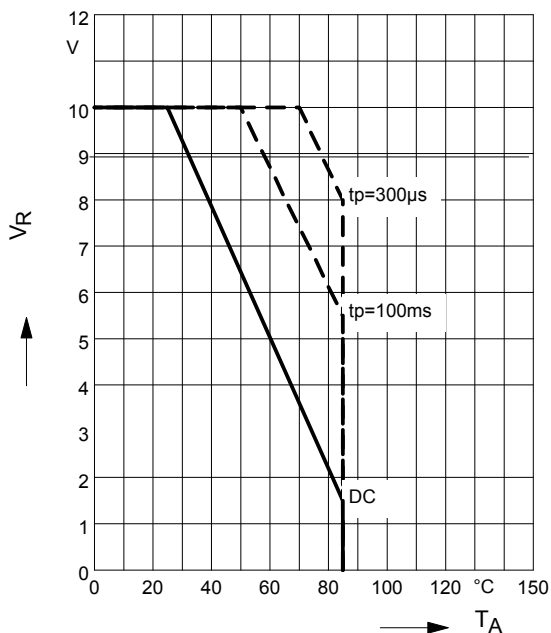
$T_A =$ Parameter



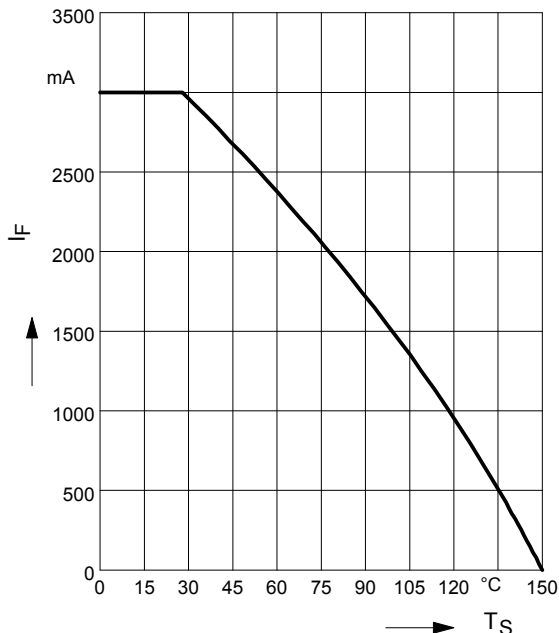
Permissible Reverse voltage $V_R = f(T_A)$

$t_p =$ Parameter; duty cycle < 0.01

Device mounted on PCB with $R_{th} = 160 \text{ K/W}$

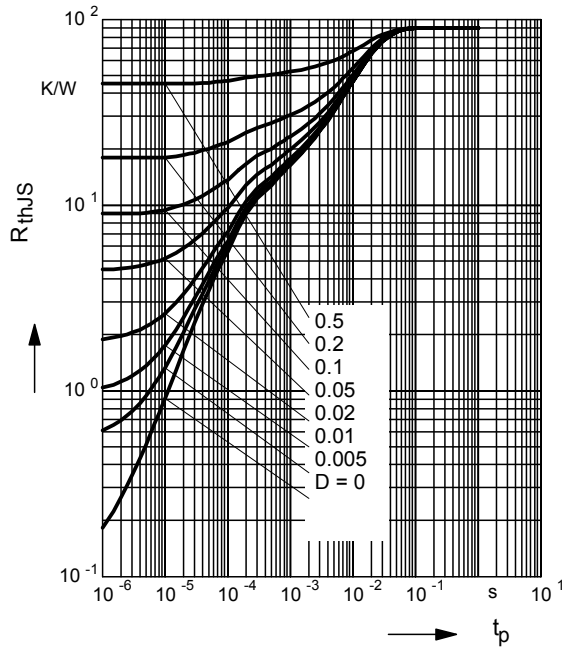


Forward current $I_F = f(T_S)$

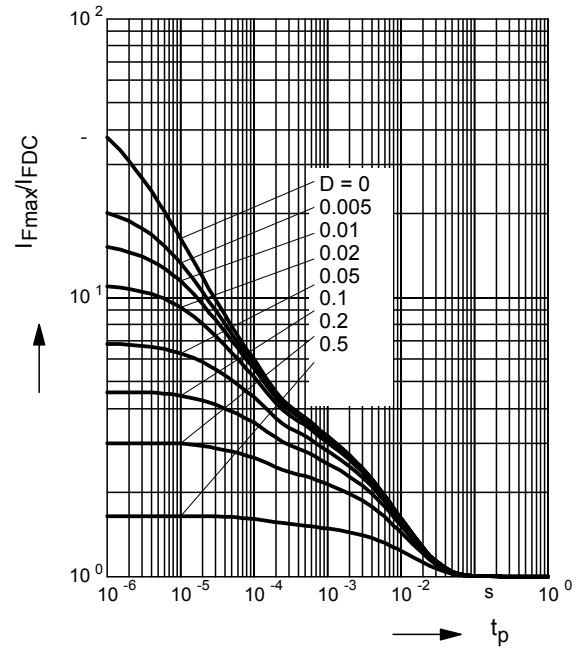


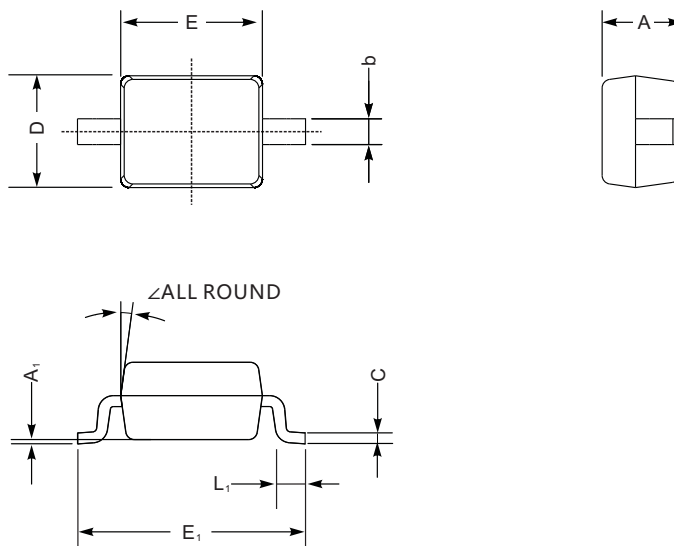
■ Typical Characteristics

Permissible Puls Load $R_{thJS} = f(t_p)$



Permissible Pulse Load $I_{Fmax} / I_{FDC} = f(t_p)$



■ SOD-323

SOD-323 mechanical data

UNIT		A	C	D	E	E ₁	b	L ₁	A ₁	∠
mm	max	1.1	0.15	1.4	1.8	2.75	0.4	0.45	0.2	9°
	min	0.8	0.08	1.2	1.4	2.55	0.25	0.2	—	
mil	max	43	5.9	55	70	108	16	16	8	
	min	32	3.1	47	63	100	9.8	7.9	—	

■ The recommended mounting pad size
